

Data Sheet June 1996 File Number 4142

7V, 7A SynchroFET™ Complementary Drive Synchronous Half-Bridge

Designed with the Pentium® in mind, the Intersil SynchroFET family provides a new approach for implementing a synchronous rectified buck switching regulator. The SynchroFET™ replaces two power DMOSs, a Schottky diode, two gate drivers and synchronous control circuitry. The complementary drive circuit turns the upper FET on and the lower FET off when the input from the PWM is high. When the input from the PWM goes low the upper FET turns off and the lower FET turns on. The HIP5016 has a PWM pin that inverts the relationship from the input to PHASE. This architecture allows the designer to utilize a low cost single-ended PWM controller in either a current or voltage mode configuration. The SynchroFET operates in continuous conduction mode reducing EMI constraints and enabling high bandwidth operation. Several features ensure easy start-up. First, the supply currents stay below specification as the supply voltages ramp up; no unexpected surges occur that might perturb a soft-start or deplete a charge-pump. Second, any power-up sequence of the V_{CC}, V_{IN}, or PWM pins can be used without causing large currents. Third, the chip operates when V_{CC} is greater than 2V so V_{CC} can be created from a charge pump powered from V_{IN}.

Ordering Information

| PART NUMBER | TEMP. RANGE (°C) | PACKAGE | PKG. NO. |
|-------------|---------------------|--------------------------------|-------------|
| HIP5015IS | -40 to 85 | 7 Ld Gullwing SIP | Z7.05B |
| HIP5015IS1 | -40 to 85 | 7 Ld Staggered Vertical SIP | Z7.05C |
| HIP5016IS | -40 to 85 | 7 Ld Gullwing SIP | Z7.05B |
| HIP5016IS1 | -40 to 85 | 7 Ld Staggered Vertical SIP | Z7.05C |

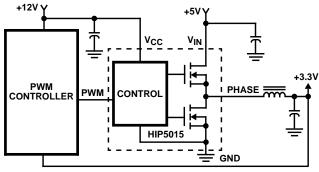
Features

- · Complementary Drive, Half-Bridge Power NMOS
- · Use With Low-Cost Single-Output PWM Controllers
- Improve Efficiency Over Conventional Buck Converter with Schottky Clamp
- Minimum Deadtime Provided by Adaptive Shoot-Through Protection Eliminates External Schottky
- Grounded Case for Low EMI and Simple Heatsinking
- Low Operating Current
- · Frequency Exceeding 1MHz
- · Dual Polarity Input Options
- · All Pins Surge Protected

Applications

- 5V to ≤3.3V Synchronous Buck Converters
- 3.3V to ≤2.9V Synchronous Buck Converters
- Pentium Power Supplies
- Bus Terminations (BTL and GTL)
- · Drive 5V Motors Directly from Microprocessor

Typical Application Block Diagram

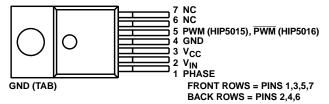


SYNCHRONOUS RECTIFIED BUCK CONVERTER

Pinouts

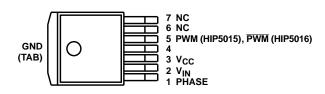
HIP5015IS1, HIP5016IS1 (SIP - VERTICAL)

TOP VIEW



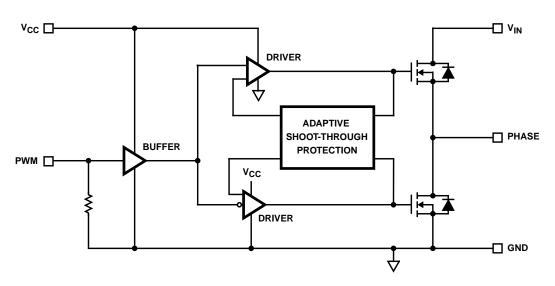
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HIP5015IS, HIP5016IS (SIP - GULLWING) TOP VIEW



Non-Inverting SynchroFET Block Diagram

HIP5015



Inverting SynchroFET Block Diagram

PWM DRIVER ADAPTIVE SHOOT-THROUGH PROTECTION PORTUGE PROTECTION GND

HIP5015, HIP5016

Absolute Maximum Ratings

| Supply Voltage, V _{CC} |
|----------------------------------------------------------|
| Input Voltage V _{IN} +7\ |
| I _{PHASE} , I _{VIN} , I _{GND} |
| PWM Input |
| ESD Classification |
| Lead Temperature (Soldering 10s) (Lead Tips Only) 300°C |
| Storage Temperature Range65°C to 150°C |
| Junction Temperature Range40°C to 150°C |

Operating Conditions

| Supply Voltage, V _{CC} | √, ±20% |
|----------------------------------------------------------------------|---------|
| Input Voltage V _{IN} | to 5.5V |
| Supply Voltage, $V_{CC.}$ minimum for charge-pumped start-up \dots | +4.0V |

Thermal Information (Typical)

| | θ _{JC} †† | | θ_{J} | _{IA} (°C/W | † | |
|-----------|--------------------|----|--------------|---------------------|----|------|
| Package | (°C/W) | 0 | 1 | 2 | 3 | 3††† |
| SIP (IS) | 2 | 55 | 30 | 25 | 24 | 18 |
| SIP (IS1) | 2 | 55 | - | - | - | - |

- Versus additional square inches of 1 ounce copper on the printed circuit board.
- $\dagger\dagger \quad \theta_{JC}$ is typical with an infinite heatsink.
- ††† 200 linear feet per minute of air flow.

| 111. | | • • • | | ٠. | • | Γ. | ٠. | ٠ | • • • | ~ | •• | • | ٠. | ~ | ••• | • | _ | ••• | • | | | | | | | | | |
|------------------|-----|-----------|--|----|-------|----|----|---|-------|-------|----|---|----|---|-----|---|---|-----|---|--|--|--|--|--|------|--|--------|---|
| I _{PHA} | SE | | | | | | | | | | | | | | | | | | | | | | | | | | 5/ | ١ |
| I_{VIN} | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
| IGNE | . (| | | | | | | | | | | | | | | | | | | | | | | | | | 3/ | ١ |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the recommended operating conditions of this specification is not implied.

Electrical Specifications

| | | | Т | յ = 25 ⁰ | С | T _J = - | 40°C -150°C | |
|---------------------------------------------|-------------------|---------------------------------------------|-----|---------------------|-----|--------------------|----------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | MIN | MAX | UNITS |
| r _{DS(ON)} Upper MOSFET | R _{DSU} | V _{CC} = 12V, V _{IN} = 5V | - | 68 | 78 | - | 130 | mΩ |
| r _{DS(ON)} Lower MOSFET | R _{DSL} | V _{CC} = 12V, V _{IN} = 5V | - | 72 | 82 | - | 136 | mΩ |
| V _{IN} Operating Current | I _{VINO} | V _{IN} = 5V, No Load, 500kHz | - | 1.8 | 4 | - | 5 | mA |
| V _{IN} Quiescent Current | I _{VIN} | PWM or PWM = V _{CC} or GND | - | 0.1 | 10 | - | 100 | μΑ |
| V _{CC} Operating Current | Icco | V _{CC} = 12V, 500kHz | - | 4.3 | 7 | - | 9 | mA |
| V _{CC} Quiescent Current (HIP5015) | Іссін | PWM = V _{CC} | - | 40 | - | - | 300 | μΑ |
| V _{CC} Quiescent Current (HIP5015) | ICCIL | PWM = GND | - | 0.1 | 10 | - | 100 | μΑ |
| V _{CC} Quiescent Current (HIP5016) | ICCNIH | PWM = V _{CC} | - | 0.1 | 10 | - | 100 | μА |
| V _{CC} Quiescent Current (HIP5016) | ICCNIL | PWM = GND | - | 100 | - | - | 300 | μΑ |
| Low Level PWM Input Voltage | V _{IL} | | - | 1.8 | - | 1 | - | V |
| High Level PWM Input Voltage | V _{IH} | | - | 2.1 | - | - | 3 | V |
| PWM Input Voltage Hysteresis | V _{IHYS} | | - | 0.3 | - | - | - | V |
| Input Pulldown Resistance (HIP5015) | R _{PWM} | | - | 220 | - | 100 | 400 | kΩ |
| Input Pullup Resistance (HIP5016) | R _{PWM} | | - | 220 | - | 100 | 400 | kΩ |

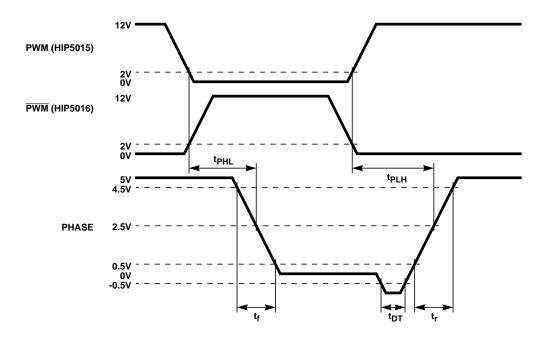
Switching Specifications

| | | | т | յ = 25 ⁰ | С | T _J = - | 40°C 150°C | |
|-----------------------------|------------------|----------------------------------------------------|-----|---------------------|-----|--------------------|---------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | MIN | MAX | UNITS |
| Upper Device Turn-Off Delay | t _{PHL} | V _{CC} = 12V, I _{PHASE} = -0.5A | - | 30 | 50 | - | 80 | ns |
| Lower Device Turn-Off Delay | t _{PLH} | V _{CC} = 12V, I _{PHASE} = +0.5A | - | 30 | 50 | - | 80 | ns |
| Dead Time | t _{DT} | V _{CC} = +12V, I _{PHASE} = -0.5A | - | 10 | - | - | - | ns |
| Phase Rise-Time | t _r | V _{CC} = 12V, I _{PHASE} = -0.5A | - | 20 | - | - | - | ns |
| Phase Fall-Time | t _f | V _{CC} = 12V, I _{PHASE} = +0.5A | - | 20 | - | - | - | ns |

Pin Descriptions

| SYMBOL | DESCRIPTION |
|--------------------------------|-------------------------------------------------------------------------------|
| V _{CC} | Positive supply to control logic and gate drivers. De-couple this pin to GND. |
| V _{IN} | FET Switch Input Voltage. De-couple this pin to GND. |
| PHASE | Output. |
| PWM (HIP5015) PWM (HIP5016) | Single Ended Control Input. This input connects to the PWM controller output. |
| GND | System Ground. |

Timing Diagram



NOTE: I_{PHASE} = +0.5A for t_{PLH} and $t_f,\ I_{PHASE}$ = -0.5A for $t_{PHL},\ t_{DT},$ and $t_f.$

FIGURE 1.

Typical Performance Curves

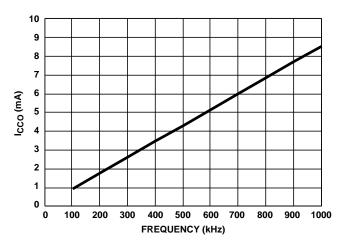


FIGURE 2. I_{CCO} vs FREQUENCY

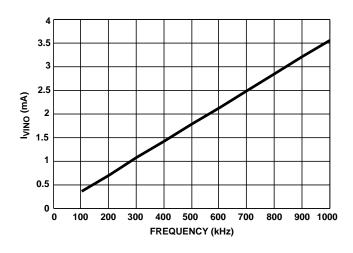


FIGURE 3. I_{VINO} vs FREQUENCY

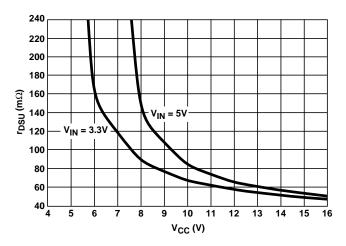


FIGURE 4. R_{DSU} vs V_{CC}

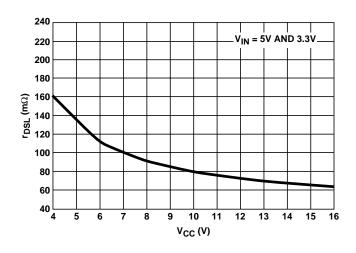


FIGURE 5. R_{DSL} vs V_{CC}

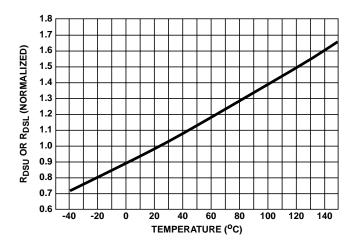


FIGURE 6. R_{DSU} OR R_{DSL} vs TEMPERATURE

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